

DS2003 High Current/Voltage Darlington Drivers General Description

The DS2003 is comprised of seven high voltage, high current NPN Darlington transistor pairs. All units feature common emitter, open collector outputs. To maximize their effectiveness, these units contain suppression diodes for inductive loads and appropriate emitter base resistors for leakage.

The DS2003 has a series base resistor to each Darlington pair, thus allowing operation directly with TTL or CMOS operating at supply voltages of 5.0V.

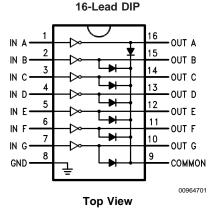
The DS2003 offers solutions to a great many interface needs, including solenoids, relays, lamps, small motors, and

LEDs. Applications requiring sink currents beyond the capability of a single output may be accommodated by paralleling the outputs.

Features

- Seven high gain Darlington pairs
- High output voltage (V_{CE} = 50V)
- High output current (I_C = 350 mA)
- TTL, PMOS, CMOS compatible
- Suppression diodes for inductive loads
- Extended temperature range

Connection Diagram



Order Numbers

N Package Number N16E	M Package Number M16A	
DS2003TN	DS2003TM	
DS2003CN	DS2003CM	

DS2003

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Storage Temperature Range	−65°C to +150°C
Operating Temperature Range	
DS2003TN, DS2003TM	−40°C to +105°C
DS2003CN, DS2003CM	0°C to +85°C
Lead Temperature	
Soldering, 10 seconds	265°C

N16E Package	1330 mW
M16A Package	770 mW
Input Voltage	-0.3V to 30V
Output Voltage	55V
Emitter-Base Voltage	6.0V
Continuous Collector Current	500 mA
Continuous Base Current	25 mA

Note: *Derate N16E package 13.3 mW/°C for T_A above 25°C. Derate M16A package 7.7 mW/°C for T_A above 25°C.

Maximum Power Dissipation* at T_A = 25°C

Electrical Characteristics

Symbol	°C, unless otherwise s Parameter	Conditions	Min	Тур	Max	Units
	Output Leakage	$T_A = 25^{\circ}C, V_{CE} = 50V$ (Figure 1)		.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	20	0
CEX	Current	$T_A = 85^{\circ}$ C, $V_{CE} = 50V$ (Figure 1) for DS2003CN, DS2003CM	_		100	μA
		$T_A = 105^{\circ}C, V_{CE} = 50V$ (Figure 1) for DS2003TN, DS2003TM			150	
V _{CE(Sat)}	Collector-Emitter	I _C = 350 mA, I _B = 500 μA (<i>Figure 3</i>) (Note 3)		1.25	1.6	
	Saturation Voltage	I _C = 200 mA, I _B = 350 μA (<i>Figure 3</i>)		1.1	1.3	V
		$I_{\rm C}$ = 100 mA, $I_{\rm B}$ = 250 µA (<i>Figure 3</i>)		0.9	1.1	1
I _{I(ON)}	Input Current	V ₁ = 3.85V (Figure 4)		0.93	1.35	mA
I _{I(OFF)}	Input Current (Note 4)	$T_A = 85^{\circ}C$ for DS2003CN, DS2003CM $I_C = 500 \ \mu A \ (Figure 5)$	50	100		μA
V _{I(ON)}	Input Voltage	$V_{CE} = 2.0V, I_{C} = 200 \text{ mA} (Figure 6)$			2.4	
	(Note 5)	V _{CE} = 2.0V, I _C = 250 mA (<i>Figure 6</i>)			2.7	V
		$V_{CE} = 2.0V, I_{C} = 300 \text{ mA} (Figure 6)$			3.0]
Cı	Input Capacitance			15	30	pF
t _{PLH}	Turn-On Delay	0.5 V ₁ to 0.5 V _O			1.0	μs
t _{PHL}	Turn-Off Delay	0.5 V_1 to 0.5 V_0			1.0	μs
I _R	Clamp Diode	$V_R = 50V$ (Figure 7) $T_A = 25^{\circ}C$			50	μA
	Leakage Current	$T_A = 85^{\circ}C$			100	μA
V _F	Clamp Diode Forward Voltage	I _F = 350 mA (<i>Figure 8</i>)		1.7	2.0	V

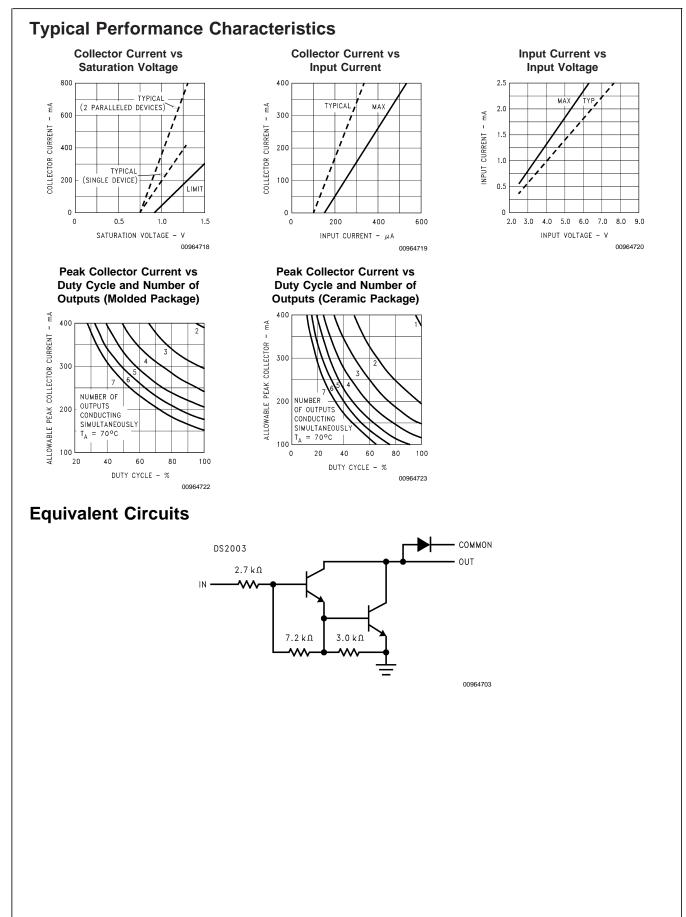
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: All limits apply to the complete Darlington series except as specified for a single device type.

Note 3: Under normal operating conditions these units will sustain 350 mA per output with V_{CE} (Sat) = 1.6V at 70°C with a pulse width of 20 ms and a duty cycle of 30%.

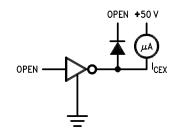
Note 4: The ${\rm I}_{\rm I(OFF)}$ current limit guaranteed against partial turn-on of the output.

Note 5: The V_{I(ON)} voltage limit guarantees a minimum output sink current per the specified test conditions.



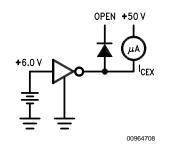
DS2003

Test Circuits



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FIGURE 1.





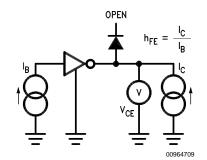


FIGURE 3.

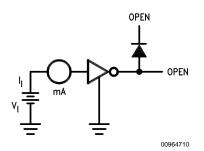


FIGURE 4.

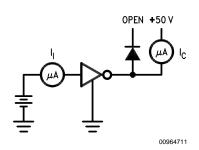


FIGURE 5.

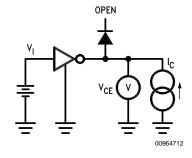


FIGURE 6.

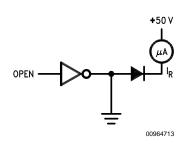


FIGURE 7.

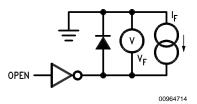
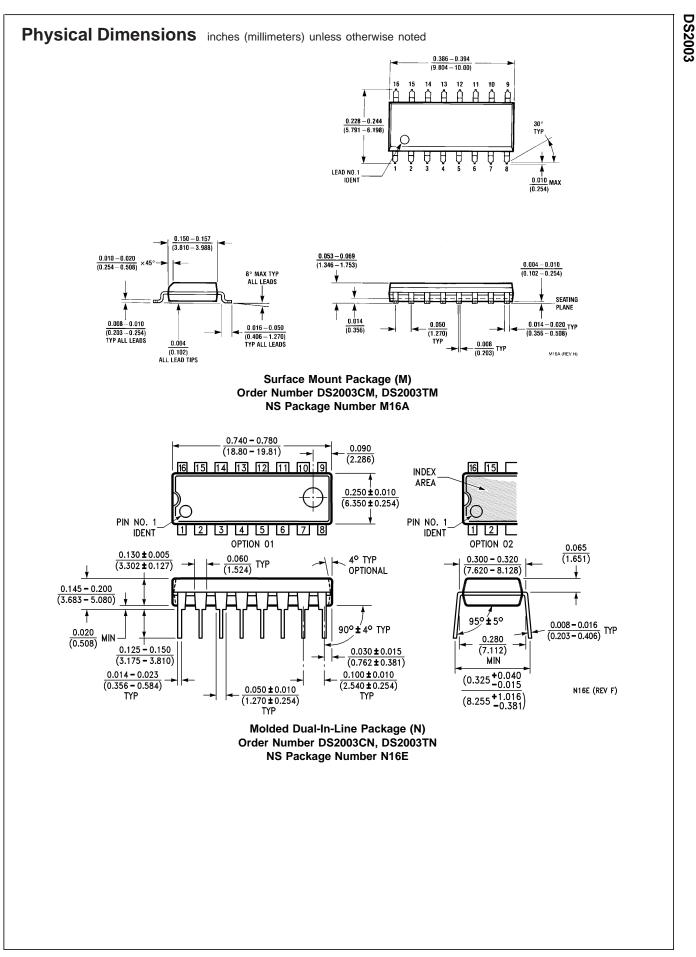


FIGURE 8.



Notes

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